

HW 2 Solutions

$$1. E_i = \frac{3kT}{4} \ln\left(\frac{m_{dh}^*}{m_{de}^*}\right) + \underbrace{\frac{E_v + E_c}{2}}_{\text{midgap}}$$

$$= \frac{3}{4} (0.02585) \ln\left(\frac{0.5492}{1.084}\right) + \text{midgap}$$

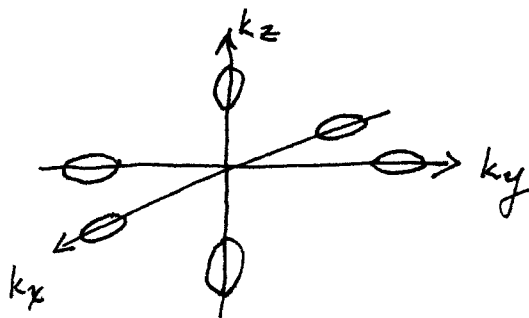
$$E_i = \text{midgap} - 13.18 \text{ meV}$$

2. a) Ga has 3 valence electrons. Si has 4.
Donor

$$b) E_{d\text{si}} = E_c - 5.8 \text{ meV}.$$

$$c) \text{ Acceptor. } E_{A\text{si}} = E_v + 38 \text{ meV}.$$

- 3) The constant energy surfaces of the conduction band in Si are ellipsoids of revolution about the 6 principal axes.



The acceleration vector in the 2 k_x valleys is

$$\begin{bmatrix} \dot{v}_x \\ \dot{v}_y \\ \dot{v}_z \end{bmatrix} = \begin{bmatrix} 1/m_t & 0 & 0 \\ 0 & 1/m_t & 0 \\ 0 & 0 & 1/m_t \end{bmatrix} \begin{bmatrix} F_x \\ F_y \\ F_z \end{bmatrix} \quad (2 k_x \text{ valleys})$$

Similarly, for the k_y & k_z valleys

$$\begin{bmatrix} \dot{v}_x \\ \dot{v}_y \\ \dot{v}_z \end{bmatrix} = \begin{bmatrix} 1/m_t & 0 & 0 \\ 0 & 1/m_t & 0 \\ 0 & 0 & 1/m_t \end{bmatrix} \begin{bmatrix} F_x \\ F_y \\ F_z \end{bmatrix} \quad (2 k_y \text{ valleys})$$

$$\begin{bmatrix} \dot{v}_x \\ \dot{v}_y \\ \dot{v}_z \end{bmatrix} = \begin{bmatrix} 1/m_t & 0 & 0 \\ 0 & 1/m_t & 0 \\ 0 & 0 & 1/m_t \end{bmatrix} \begin{bmatrix} F_x \\ F_y \\ F_z \end{bmatrix} \quad (2 k_z \text{ valleys})$$

The average electron acceleration due to the response of all 6 valleys is

$$\langle \dot{\vec{v}} \rangle = \frac{1}{6} \sum_{i=1}^6 \dot{\vec{v}}_i$$

Thus

$$\begin{bmatrix} \langle \dot{v}_x \rangle \\ \langle \dot{v}_y \rangle \\ \langle \dot{v}_z \rangle \end{bmatrix} = \begin{bmatrix} 2/m_t + 1/m_l & 0 & 0 \\ 0 & 2/m_t + 1/m_l & 0 \\ 0 & 0 & 2/m_t + 1/m_l \end{bmatrix} \left(\frac{1}{3} \right) \begin{bmatrix} F_x \\ F_y \\ F_z \end{bmatrix}$$

$$\text{or } \langle \dot{\vec{v}} \rangle = \frac{1}{3} \left(\frac{2}{m_t} + \frac{1}{m_l} \right) \vec{F}$$

Thus, the acceleration vector is co-linear with the force vector for an arbitrary force direction. Hence, the

electronic conduction is isotropic.

4) (a) The conductivity effective mass is defined by the above force equation, solution to (1).

(b) $m_l^* = 0.98$, $m_t^* = 0.19$

$$m_{ce}^* = 3 \left(\frac{2}{m_t} + \frac{1}{m_l} \right)^{-1} = \boxed{0.260 m_0}$$

5) GaAs

$$\boxed{m_{de}^* = m_{ce}^* = 0.067 m_0}$$

Ge

$$m_l^* = 1.64, \quad m_t^* = 0.082$$

$$m_{ce}^* = 3 \left(\frac{2}{m_t} + \frac{1}{m_l} \right)^{-1} = \boxed{0.12 m_0}$$

$$m_{de}^* = \left[M^{2/3} (m_l m_t^2)^{1/3} \right] = 4^{2/3} \left[(1.64)(0.082)^2 \right]^{1/3}$$

$$\boxed{m_{de}^* = 0.561 m_0}$$

(6) $\mu = \frac{e \tau}{m_{ce}^*} = 200 \frac{\text{cm}^2}{\text{Vs}} = 0.02 \frac{\text{m}^2}{\text{Vs}}$

$$\tau = 0.02 \frac{m_{ce}^*}{e} = \frac{0.02 (0.260) (9.11 \times 10^{-31})}{1.602 \times 10^{-19}}$$

$$\tau = 2.957 \times 10^{-14} \text{ s}$$

$$\boxed{\tau = 29.6 \text{ fs}}$$

(7) GaAs $\mu = \frac{e \tau}{m_{ce}^*} = \frac{e}{0.067 m_0} \tau = \boxed{776 \frac{\text{cm}^2}{\text{Vs}}}$

Ge $\mu = \frac{e \tau}{0.12 m_0} = \boxed{433 \frac{\text{cm}^2}{\text{Vs}}}$

$$(8) (a) p = N_V e^{-(E_F - E_V)/kT} \quad \text{at } 300K \quad N_A = 2 \times 10^{16} / \text{cm}^3$$

$$p = p_{LH} + p_{HH}$$

$$N_V = N_{V_{LH}} + N_{V_{HH}}$$

$$p_{LH} = \frac{N_{V_{LH}}}{N_V} N_A = \frac{m_{LH}^{3/2}}{m_{LH}^{3/2} + m_{HH}^{3/2}} N_A$$

$$p_{LH} = \frac{(0.082)^{3/2}}{(0.082)^{3/2} + (0.45)^{3/2}} (2 \times 10^{16})$$

$$\boxed{p_{LH} = 1.44 \times 10^{15} / \text{cm}^3}$$

$$(b) E_F - E_V = -kT \ln\left(\frac{N_0}{N_V}\right) = 0.026 \ln\left(\frac{7 \times 10^{18}}{2 \times 10^{16}}\right)$$

$$\boxed{E_F = E_V + 0.152 \text{ eV}}$$

9.) In steady state $R = G = 10^{22}/\text{cm}^3\text{s}$

$$R = \frac{np - n_i^2}{\tau_n(n + n_i e^{(E_T - E_i)/kT}) + \tau_p(p + n_i e^{(E_i - E_T)/kT})}$$

midgap $\Rightarrow E_i \approx E_T$
also $\tau_n = \tau_p = \tau$.

NB: Minority carrier diffusion equations are NOT valid here since $n_0 = p_0 = n_i$ & $\Delta n = \Delta p \gg n_i$.

$$R = \frac{np - n_i^2}{\tau(n + p + 2n_i)}$$

$$n = n_0 + \Delta n$$

$$p = p_0 + \Delta p$$

$$R = \frac{\cancel{n_0 p_0} + n_0 \Delta p + p_0 \Delta n + \Delta n \Delta p - n_i^2}{\tau(n_0 + \Delta n + p_0 + \Delta p + 2n_i)}$$

$$\Delta n = \Delta p$$

$$R = \frac{(n_0 + p_0)\Delta n + (\Delta n)^2}{\tau(n_0 + p_0 + 2\Delta n + 2n_i)}$$

The doping of $2e6/\text{cm}^3$ is negligible compared to n_i , so $n_0 = p_0 = n_i$.

$$R = \frac{2n_i \Delta n + (\Delta n)^2}{\tau(4n_i + 2\Delta n)} = \frac{\Delta n(2n_i + \Delta n)}{\tau 2(2n_i + \Delta n)}$$

$$\boxed{\Delta n = 2R\tau = 2e6/\text{cm}^3 = \Delta p}$$

10. No. Au is a midgap state in Si - an efficient R-G center.

11. a) $10^{18}/\text{cm}^3 \Rightarrow 0.02 \Omega\text{cm}$
b) $2.5 \times 10^{15}/\text{cm}^3$ } From Fig. 21 of Sze
p. 32.